

- ☒ Original
☐ Continuation
☐ Division
☐ Continuation-in-part
☐ Supplemental

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

Low Power Current Input Delta-Sigma ADC Using Injection FET Reference

the specification of which

(check one) ☒ is attached hereto.
☐ was filed on _____ as Application No. _____ and (a) [other than supplemental] was amended on _____ or (b) [supplemental] with amendments through n/a.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, §119 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)

Number	Country	Day/Month/Year Filed	Priority Claimed
			<input type="checkbox"/> Yes <input type="checkbox"/> No

I hereby claim the benefit under Title 35, United States Code, §120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code §112, I acknowledge the duty to disclose to the United States Patent and Trademark Office all information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations, §1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application:

Application Serial No.	Filing Date	Status
		(patented, pending, abandoned)

Raytheon Company

Intellectual Property & Licensing, Loc: **EO/E04/N119**

2000 East El Segundo Boulevard, P. O. Box 902

El Segundo CA 90245-0902, Attorney: W. C. Schubert (805) 562-2685 phone

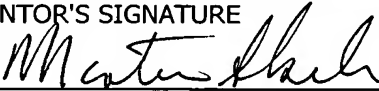
re: Low Power Current Input Delta-Sigma ADC Using Injection FET Reference

I hereby appoint the following attorneys, or agent and attorneys, to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

William C. Schubert	Registration No. 30,102
Glenn H. Lenzen, Jr.	Registration No. 29,320
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Address all correspondence to Intellectual Property & Licensing, Raytheon Company, Bldg. EO/E04 M/S N119, P.O. Box 902, El Segundo, California 90245-0902. Address all telephone calls to William C. Schubert, 805-562-2108, Raytheon Company, Goleta, California 93117.

I HEREBY DECLARE THAT ALL STATEMENTS MADE HEREIN OF MY OWN KNOWLEDGE ARE TRUE AND THAT ALL STATEMENTS MADE ON INFORMATION AND BELIEF ARE BELIEVED TO BE TRUE; AND FURTHER THAT THESE STATEMENTS WERE MADE WITH THE KNOWLEDGE THAT WILLFUL FALSE STATEMENTS AND THE LIKE SO MADE ARE PUNISHABLE BY FINE OR IMPRISONMENT, OR BOTH, UNDER SECTION 1001 OF TITLE 18 OF THE UNITED STATES CODE AND THAT SUCH WILLFUL FALSE STATEMENTS MAY JEOPARDIZE THE VALIDITY OF THE APPLICATION OR ANY PATENT ISSUED THEREON.

FULL NAME OF SOLE OR JOINT INVENTOR Christopher L. Fletcher	INVENTOR'S SIGNATURE	DATE
RESIDENCE (CITY AND STATE) Santa Barbara, California	CITIZENSHIP USA	
POST OFFICE ADDRESS 4121 Sycamore Canyon Road, Santa Barbara, California 93108		
FULL NAME OF SOLE OR JOINT INVENTOR Martins Skele	INVENTOR'S SIGNATURE 	DATE Jan 27, 2004
RESIDENCE (CITY AND STATE) Langley, Washington	CITIZENSHIP USA	
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FULL NAME OF SOLE OR JOINT INVENTOR	INVENTOR'S SIGNATURE	DATE
RESIDENCE (CITY AND STATE)	CITIZENSHIP	
POST OFFICE ADDRESS		

WCS:NCS/RVS/GOLETA

*Government contract related N66001-02-C-8087

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January 29, 2004

TO: Office of Patent Counsel
Attention: James A. Ward
SPAWARSYSCEN Code D0012
53510 Silver Gate Avenue
San Diego CA 92152-5765

SUBJECT: *Contract No. N66001-02-C-8078

1. The invention disclosure identified below was made in the performance of the subject contract:

Raytheon Attorney Docket No.	Title	Inventor(s)
03W089*	LOW POWER CURRENT DELTA- SIGMA ADC USING INJECTION FET REFERENCE	Christopher L. Fletcher Martins Skele

2. The Contractor has filed a patent application on the subject invention disclosure.
3. For your information and records, one copy of the patent application is enclosed herewith describing the invention and bearing Contractor's identification No. 03W089. The classification of this application is believed to be "unclassified".



WILLIAM C. SCHUBERT

Senior Intellectual Property Counsel

In duplicate

WCS:ssf:X-5.gvt.appl

Enclosures: Patent Application 03W089* including 6 sheets of drawings with transmittal letter to the United States Patent and Trademark Office (Form PTO/SB/05)

cc: S. Williams EO/E04/N119 w/o encls.
Lynn Hyatt SB/B6/11 w/o encls. (BEAR)

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